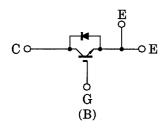
TOSHIBA GTR Module Silicon N Channel IGBT

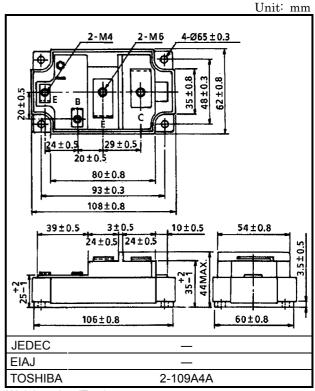
MG240V1US41

High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case
- High input impedance
- Enhancement-mode
- High speed : $t_f = 1.5 \mu s \text{ (Max.)} (I_C = 240 \text{A})$ $t_{rr} = 0.6 \mu s \text{ (Max.)} (I_F = 240 \text{A})$

Equivalent Circuit





Weight: 465g(Typ.)

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1700	٧	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	I _C	240	А	
	1ms	I _{CP}	480		
Forward current	DC	I _F	240	Α	
	1ms	I _{FM}	480		
Collector power dissipation (Tc = 25°C)		PC	2400	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	4000 (AC 1 min.)	V	
Screw torque (M4/M6 / mounting)		_	2/3/3	N·m	

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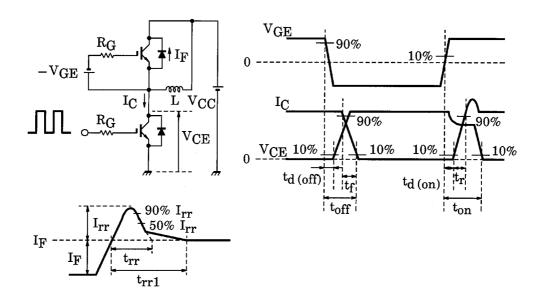
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Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0	_	_	±200	nA
Collector cut-off current		I _{CES}	V _{CE} = 1700V, V _{GE} = 0	_	_	2.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 240mA, V _{CE} = 5V	4.0	_	8.0	V
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 240A,V _{GE} = 15V	_	3.2	4.5	V
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	_	32800	_	pF
Switching time	Turn-on delay time	t _{d (on)}	Inductive load $V_{CC} = 900V$ $I_{C} = 240A$ $V_{GE} = \pm 15V$ $R_{G} = 2.4\Omega$ (Note 1)	_	0.1	_	- µs
	Rise time	t _r		_	0.1	_	
	Turn-on time	t _{on}		_	0.5	_	
	Turn-off delay time	t _{d (off)}		_	0.4	_	
	Fall time	t _f		_	0.5	1.5	
	Turn-off time	t _{off}		_	1.0	_	
Forward voltage		V _F	I _F = 240A, V _{GE} = 0	_	3.7	5.0	V
Reverse recovery time		t _{rr}	I _F = 240A, V _{GE} = -15V di / dt = 1000A / µs (Note 1)	_	0.3	0.6	μs
Thermal resistance		R _{th (j-c)}	Transistor stage	_	_	0.052	°C/W
			Diode stage	_	_	0.2	

Note 1: Switching time and reverse recovery time test circuit & timing chart

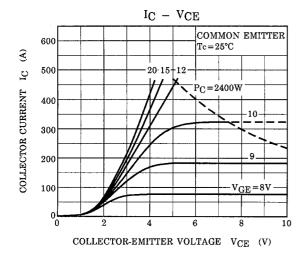


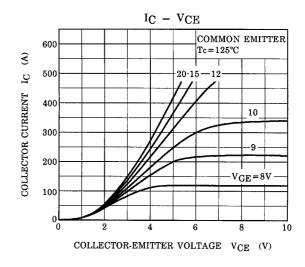
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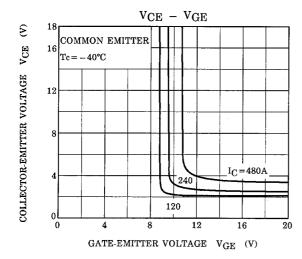
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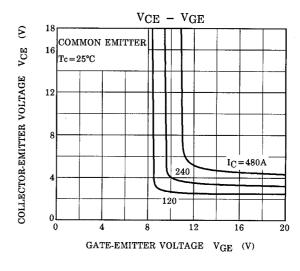
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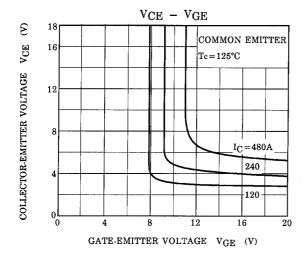
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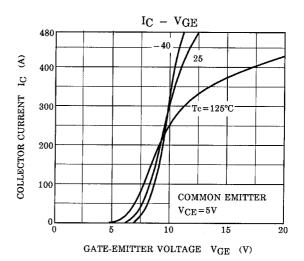


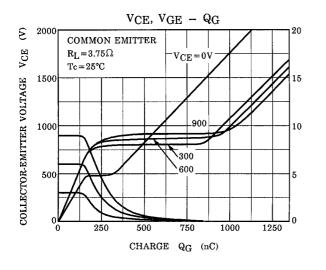


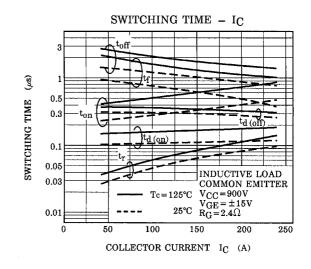












3

 V_{GE}

GATE-EMITTER VOLTAGE

